

2N5545/46/47/JANTX/JANTXV

Monolithic N-Channel JFET Duals

Product Summary

Part Number	V _{GS(off)} (V)	V _{(BR)GSS} Min (V)	g _{fs} Min (mS)	I _G Max (pA)	V _{GS1} - V _{GS2} Max (mV)
2N5545	-0.5 to -4.5	-50	1.5	-50	5
2N5546	-0.5 to -4.5	-50	1.5	-50	10
2N5547	-0.5 to -4.5	-50	1.5	-50	15

Features

- Monolithic Design
- High Slew Rate
- Low Offset/Drift Voltage
- Low Gate Leakage: 3 pA
- Low Noise
- High CMRR: 100 dB

Benefits

- Tight Differential Match vs. Current
- Improved Op Amp Speed, Settling Time Accuracy
- Minimum Input Error/Trimming Requirement
- Insignificant Signal Loss/Error Voltage
- High System Sensitivity
- Minimum Error with Large Input Signal

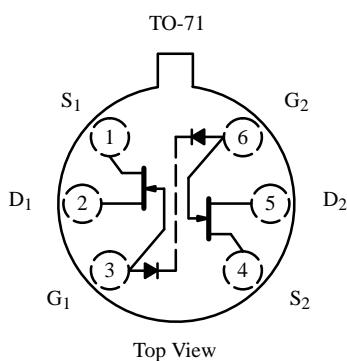
Applications

- Wideband Differential Amps
- High-Speed, Temp-Compensated, Single-Ended Input Amps
- High-Speed Comparators
- Impedance Converters

Description

The 2N5545/5546/5547JANTX/JANTXV are monolithic dual n-channel JFETs designed to provide high input impedance ($I_G < 50$ pA) for general-purpose differential amplifiers. The 2N5545 features minimum system error and calibration (5-mV offset maximum).

The TO-71 package is available with full military processing (see Military Information).



Absolute Maximum Ratings

Gate-Drain, Gate-Source Voltage	-50 V
Gate Current	30 mA
Lead Temperature (1/16" from case for 10 sec.)	300°C
Storage Temperature	-65 to 200°C
Operating Junction Temperature	-55 to 150°C

Power Dissipation :	Per Side ^a	250 mW
	Total ^b	500 mW

Notes

- a. Derate 2 mW/°C above 25°C
- b. Derate 4 mW/°C above 25°C

Updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #70253.

2N5545/46/47/JANTX/JANTXV

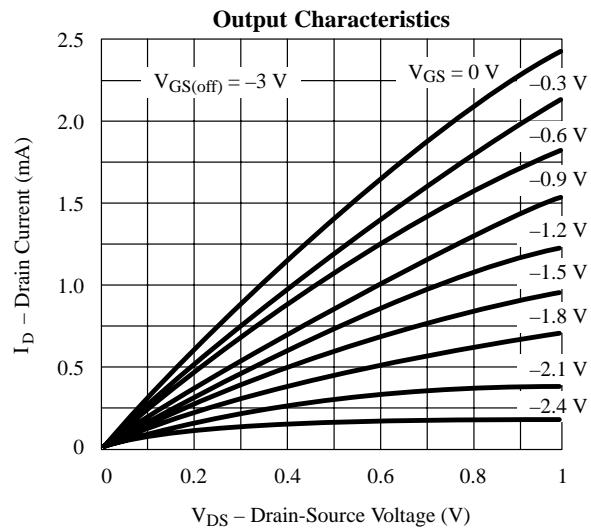
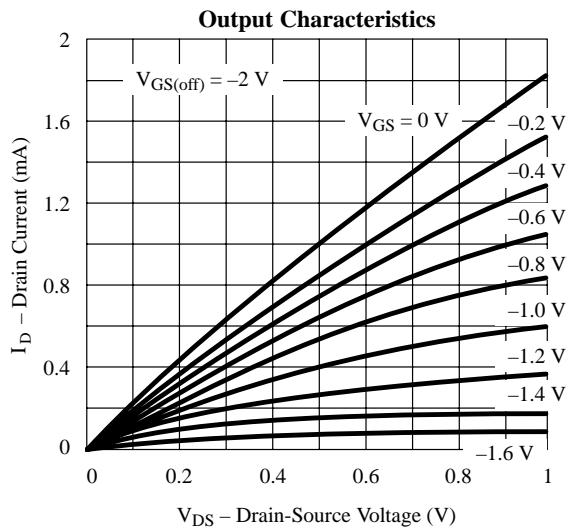
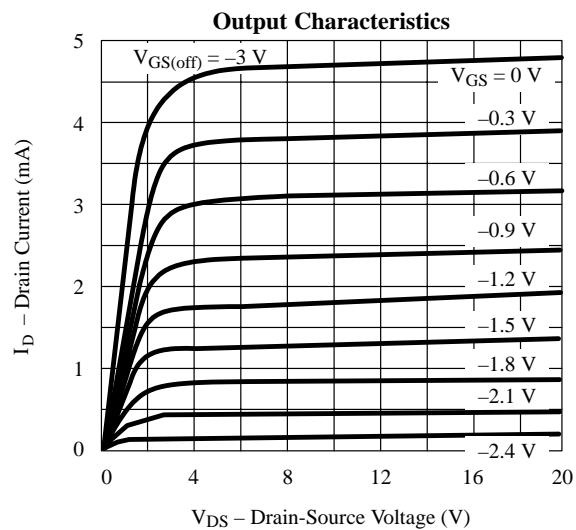
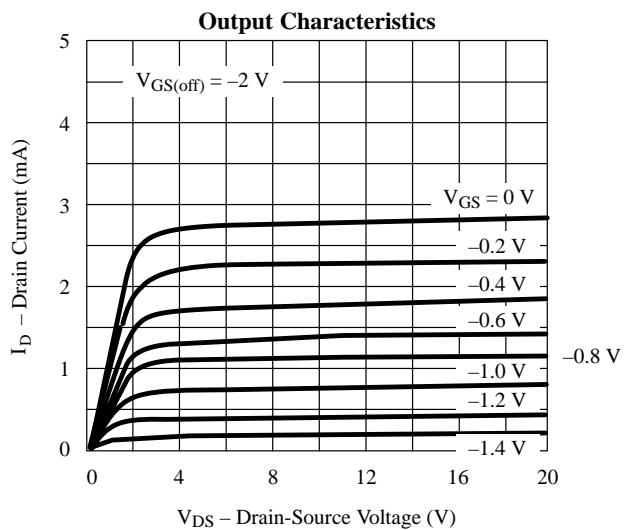
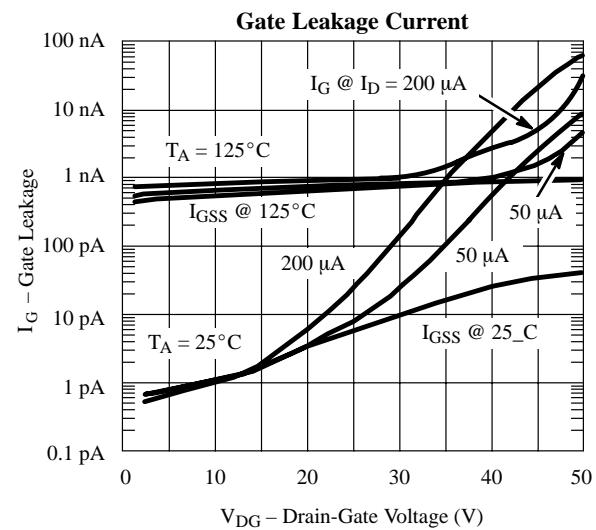
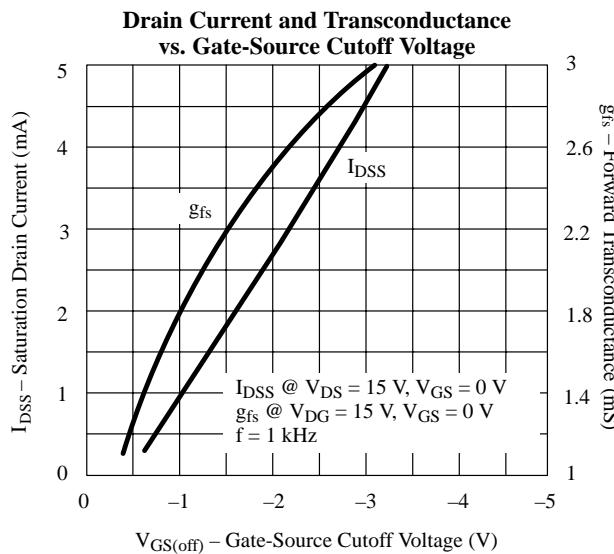
Specifications^a

Parameter	Symbol	Test Conditions	Typ ^b	Limits						Unit
				2N5545		2N5546		2N5547		
Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Static										
Gate-Source Breakdown Voltage	V _{(BR)GSS}	I _G = -1 μA, V _{DS} = 0 V	-57	-50		-50		-50		V
Gate-Source Cutoff Voltage	V _{GS(off)}	V _{DS} = 15 V, I _D = 0.5 nA	-2	-0.5	-4.5	-0.5	-4.5	-0.5	-4.5	
Saturation Drain Current ^c	I _{DSS}	V _{DS} = 15 V, V _{GS} = 0 V	3	0.5	8	0.5	8	0.5	8	mA
Gate Reverse Current	I _{GSS}	V _{GS} = -30 V, V _{DS} = 0 V T _A = 150°C	-10		-100		-100		-100	pA
		T _A = 150°C	-20		-150		-150		-150	nA
Gate Operating Current	I _G	V _{DG} = 15 V, I _D = 200 μA	-3		-50		-50		-50	pA
Gate-Source Forward Voltage	V _{GS(F)}	I _G = 1 mA, V _{DS} = 0 V	0.7							V
Dynamic										
Common-Source Forward Transconductance ^c	g _{fs}	V _{DS} = 15 V, V _{GS} = 0 V f = 1 kHz	2.5	1.5	6.0	1.5	6.0	1.5	6.0	mS
Common-Source Output Conductance ^c	g _{os}		2		25		25		25	μS
Common-Source Input Capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V f = 1 MHz	3.5		6		6		6	pF
Common-Source Reverse Transfer Capacitance	C _{rss}		1.3		2		2		2	
Equivalent Input Noise Voltage	ē _n	V _{DS} = 15 V, I _D = 200 μA f = 10 Hz	20		180		200			nV/√Hz
Noise Figure	NF	R _G = 1 MΩ	0.1		3.5		5			dB
Matching										
Differential Gate-Source Voltage	V _{G7S1} - V _{G8S2}	V _{DG} = 15 V, I _D = 50 μA			5		10		15	mV
		V _{DG} = 15 V, I _D = 200 μA			5		10		15	
Gate-Source Voltage Differential Change with Temperature	$\frac{\Delta V_{GS1} - V_{GS2} }{\Delta T}$	V _{DG} = 15 V, I _D = 200 μA T _A = -55 to 125°C			10		20		40	μV/°C
Saturation Drain Current Ratio ^d	$\frac{I_{DSS1}}{I_{DSS2}}$	V _{DS} = 15 V, V _{GS} = 0 V	0.98	0.95	1	0.9	1	0.9	1	
Transconductance Ratio ^d	$\frac{g_{fs1}}{g_{fs2}}$	V _{DS} = 15 V, I _D = 200 μA f = 1 kHz	0.99	0.97	1	0.95	1	0.9	1	
Differential Output Conductance	g _{os1} - g _{os2}	V _{DG} = 15 V, V _{GS} = 0 V f = 1 kHz	0.1		1		2		3	μS
Differential Gate Current	I _{G1} - I _{G2}	V _{DG} = 15 V, I _D = 200 μA T _A = 125°C	1		5		5		5	nA

Notes

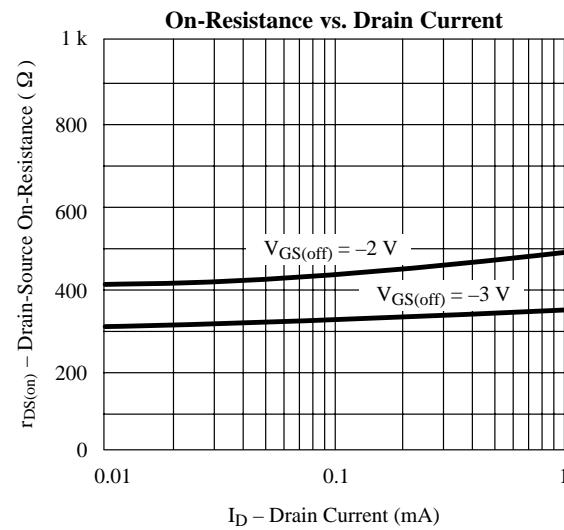
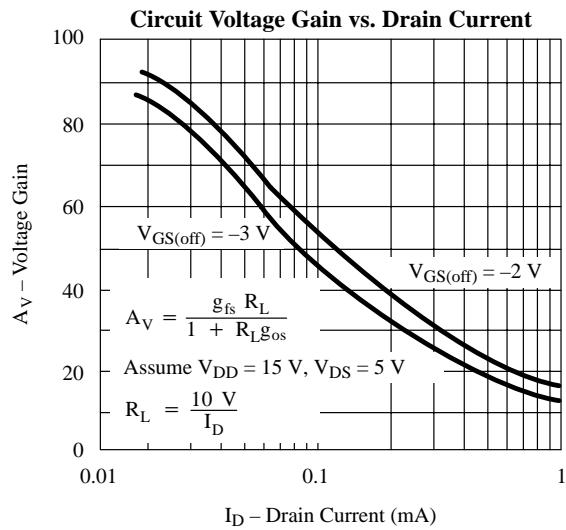
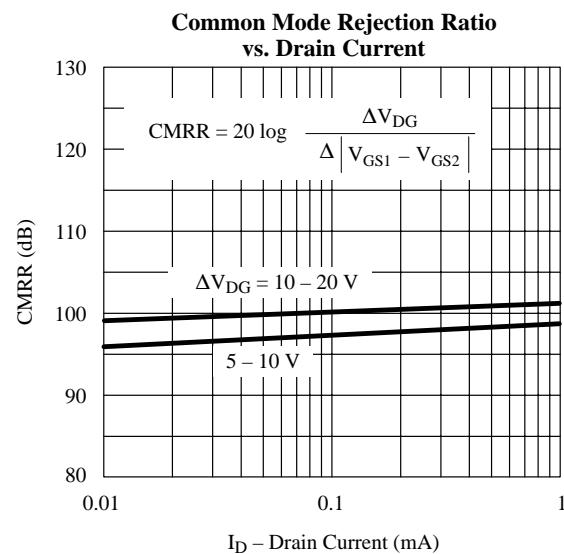
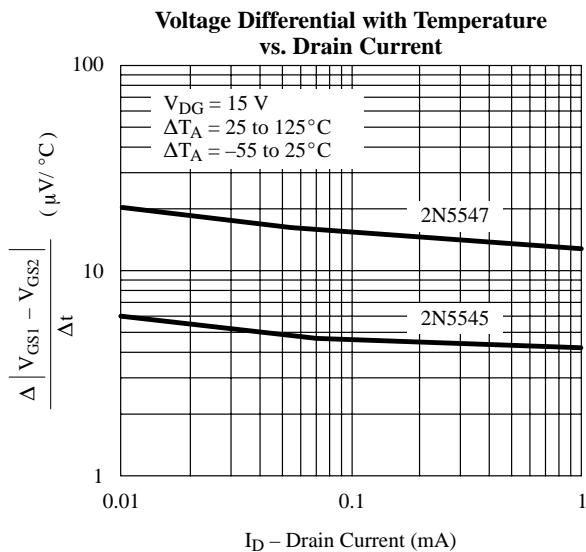
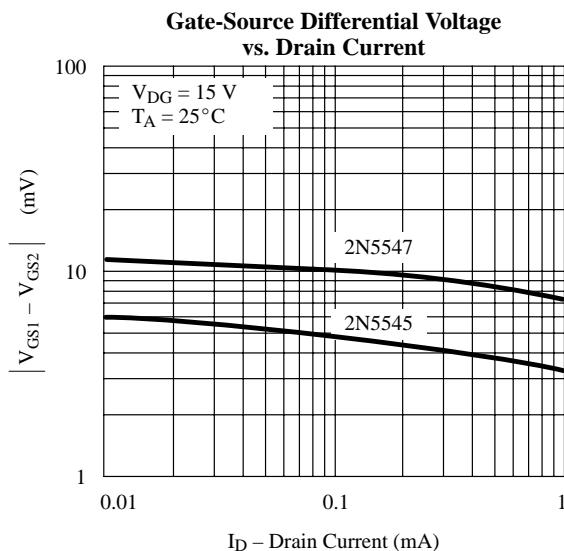
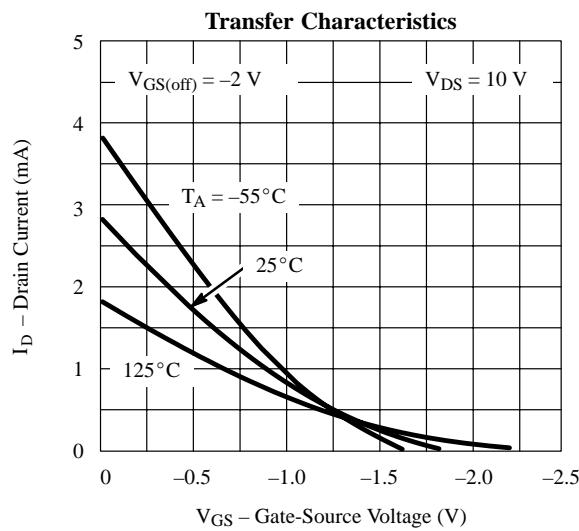
- a. T_A = 25°C unless otherwise noted.
- b. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- c. Pulse test: PW ≤ 300 μs duty cycle ≤ 3%.
- d. Assumes smaller value in the numerator.

Typical Characteristics



2N5545/46/47/JANTX/JANTXV

Typical Characteristics (Cont'd)



2N5545/46/47/JANTX/JANTXV

Typical Characteristics (Cont'd)

